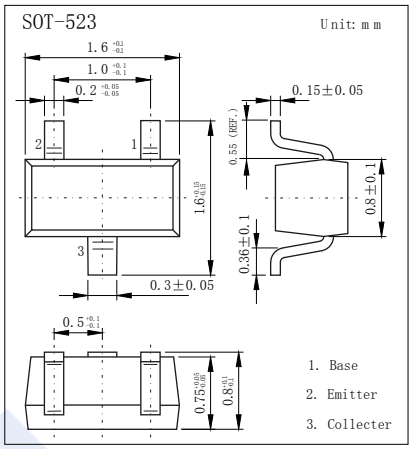
PNP Transistors

2SA1774



■ Features

- Reduces Board Space
- High h_{FE}
- Low $V_{CE(sat)}$

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -50 μA, I_E=0	-60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-50			
Emitter - base breakdown voltage	V_{EBO}	I_E= -50 μ A, I_C=0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -60 V , I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -6V , I_C=0			-100	
Collector-emitter saturation voltage (Note.1)	$V_{CE(sat)}$	I_C=-50 mA, I_B=-5mA			-0.5	V
Base - emitter saturation voltage (Note.1)	$V_{BE(sat)}$	I_C=-50 mA, I_B=-5mA			-1.2	
DC current gain	h_{FE}	V_{CE}= -6V, I_C= -1mA	120		560	
Collector output capacitance	C_{ob}	V_{CB}= -12V, I_E= 0mA,f=1MHz		3.5	5	pF
Transition frequency	f_T	V_{CE}= -12V, I_C= -2mA,f=30MHz		140		MHz

■ Classification of h_{fe}

Type	2SA1774-Q	2SA1774-R	2SA1774-S
Range	120-270	180-390	270-560
Marking	FQ	FR	FS

PNP Transistors

2SA1774

■ Typical Characterisitics

